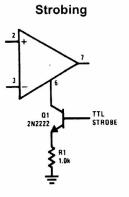


TYPICAL APPLICATIONS³

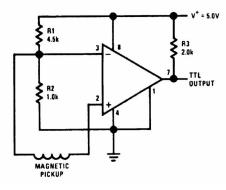
Offset Balancing

R1 R1 5 5 k 7 7

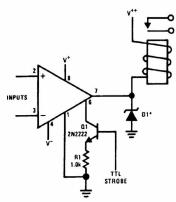


 $\ensuremath{\textbf{Note:}}$ Do Not Ground Strobe Pin. Output is turned off when current is pulled from Strobe Pin.

Detector for Magnetic Transducer

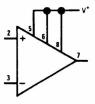


Relay Driver with Strobe

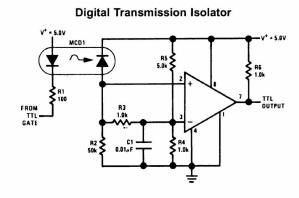


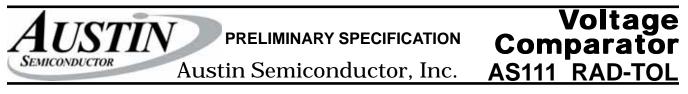
*Absorbs inductive kickback of relay and protects IC from severe voltage transients on V** line. Note: Do Not Ground Strobe Pin.

Increasing Input Stage Current (Note 1)



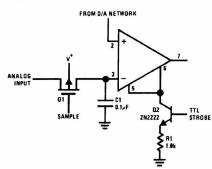
Note 1: Increases typical common mode slew from 7.0V/µs to 18V/µs.



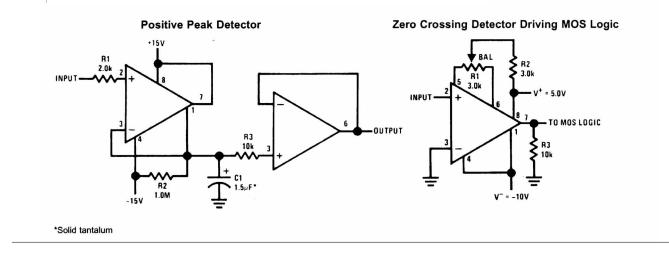


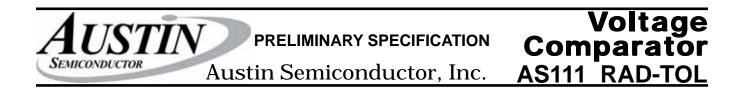
TYPICAL APPLICATIONS (CONTINUED)³

Strobing off Both Input and Output Stages (Note 2)



NOTE: Do Not Ground Strobe Pin NOTE 2: Typical input current is 50pV with inputs strobed off. NOTE 3: Pin connections shown on schematic diagram and typical applications are for TO08 metal can package.





ABSOLUTE MAXIMUM RATINGS*,5

Operating Temperature Range
Maximum Junction Temperature+175C
Storage Temperature Range $-65C \le Ta \le +150C$
Lead Temperature (soldering for 60 sec) 300C
Total Supply Voltage (V ₈₄)
Output to Negative Supply Voltage (V ₇₄)50V
Ground to Negative Supply Voltage (V_{14})
Differential Input Voltage±30V
Input Voltage ⁴ ±15V
Output Short Circuit Duration
Lead Temperature (Soldering, 10 sec)
Voltage at Stobe Pin V^+ -5V
Maximum Strobe Current 10mA
Sink Current
Package Weight:
10 Lead Cerpack Flatpak 240mg
10 Lead Cerpack Gullwing 220mg
8 Lead Metal Can 950mg
8 Lead Cerdip 1100mg

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Note 4: This rating applies for ± 15 supplies. The positive input voltage limit is 30V above the negative supply. The negative input voltage limit is equal to the negative supply voltage or 30V below the positive supply, whichever is less.

Note 5: The maximum junction temperature of the AS111 is 175°C. For operating at elevated temperatures, devices in the TO08 package must be derated based on a thermal resistance of 160°C/W, junction to ambient, or 50°C/W, junction to case. The thermal resistance of the C008 dual-in-line package is 130°C/W, junction to ambient, and 20°C/W Junction to Case. The thermal resistance of the CP10 Cerpack Flatpak & the GW10 Cerpack Gullwing are 230°C/W for juntion to ambient and 25°C/W Junction to Case. These figures are based on Still Air & 1/2 Watt power dissipation.

(The following Table applies to the Subgroup column in the Electrical Characteristics Tables)

<u>SUBGROUP</u>	Description	<u>TEMP(ºC)</u>
1	Static DC tests	+25
2	Static DC tests	+125
3	Static DC tests	-55
4	Dynamic Tests	+25
5	Dynamic Tests	+125
6	Dynamic Tests	-55
7	Functional Tests	+25
8	Functional Tests	+125
9	Functional Tests	-55

Voltage Comparator AS111 RAD-TOL

Austin Semiconductor, Inc.

Electrical Characteristics

USTIN

SEMICONDUCTOR

DC PARAMETERS: (SEE NOTE 8)

(The following conditions apply to all the following parameters, unless otherwise specified.) DC: $\pm Vcc$ = $\pm 15V,~Vcm$ = 0V

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Vio Input Offset Voltage	Vin = 0V, Rs = 50 Ohms			- 3	+3	mV	1	
					-4	+4	mV	2, 3
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50 Ohms			-3	+3	mV	1
					-4	+4	mV	2, 3
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50 Ohms			- 3	+3	mV	1
					-4	+4	mV	2, 3
		+Vcc = +2.5V, -Vcc = -2.5V, Vin = 0V, Rs = 50 Ohms			- 3	+3	mV	1
					-4	+4	mV	2, 3
Vio(R)	Raised Input Offset Voltage	Vin = 0V, Rs = 50 Ohms			- 3	+3	mV	1
	l libbe versage				-4.5	+4.5	mV	2, 3
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50 Ohms			- 3	+3	mV	1
					-4.5	+4.5	mV	2, 3
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50 Ohms			- 3	+3	mV	1
					-4.5	+4.5	mV	2, 3
Iio	Input Offset Current	Vin = OV, Rs = 50K Ohms			-10	+10	nA	1, 2
					-20	+20	nA	3
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50K Ohms			-10	+10	nA	1, 2
					-20	+20	nA	3
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50K Ohms			-10	+10	nA	1, 2
					-20	+20	nA	3
Iio(R)	Raised Input Offset Current	Vin = 0V, Rs = 50K Ohms			-25	+25	nA	1, 2
					-50	+50	nA	3
Iib+	Input Bias Current	Vin = OV, Rs = 50K Ohms			-100	0.1	nA	1, 2
					-150	0.1	nA	3
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50K Ohms			-150	0.1	nA	1, 2
					-200	0.1	nA	3
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50K Ohms			-150	0.1	nA	1, 2
					-200	0.1	nA	3

Voltage Comparator

AS111 RAD-TOL

Austin Semiconductor, Inc.

Electrical Characteristics

USTIN

SEMICONDUCTOR

DC PARAMETERS: (SEE NOTE 8) (Continued)

(The following conditions apply to all the following parameters, unless otherwise specified.) DC: $\pm Vcc$ = $\pm 15V,$ Vcm = 0V

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Iib-	Input Bias Current	Vin = 0V, Rs = 50K Ohms			-100	0.1	nA	1, 2
					-150	0.1	nA	3
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50K Ohms			-150	0.1	nA	1, 2
					-200	0.1	nA	3
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50K Ohms			-150	0.1	nA	1, 2
					-200	0.1	nA	3
Vo(STB)	Collector Output Voltage (ST)	Vin+ = Gnd, Vin- = 15V, Istb = -3mA, Rs = 50 Ohms	1		14		V	1, 2, 3
CMR	Common Mode Rejection	-28V <u><</u> -VCC <u><</u> -0.5V, Rs=50 Ohms, 2V <u><</u> +VCC <u><</u> 29.5V, Rs=50 Ohms, -14.5V <u><</u> VCm <u><</u> 13V,Rs=50 Ohms			80		dB	1, 2, 3
Vol	Low Level Output Voltage	+Vcc = 4.5V, -Vcc = Gnd, Iout = 8mA, <u>+</u> Vin = 0.5V, Vid = -6mV				0.4	V	1, 2, 3
		+Vcc = $4.5V$, -Vcc = Gnd, Iout = $8mA$, <u>+</u> Vin = $3V$, Vid = $-6mV$				0.4	V	1, 2, 3
		Iout = 50mA, \pm Vin = 13V, Vid = -5mV				1.5	V	1, 2, 3
		Iout = 50mA, \pm Vin = -14V, Vid = -5mV				1.5	V	1, 2, 3
Icex	Output Leakage Current	+Vcc = 18V, -Vcc = -18V, Vout = 32V			-1	10	nA	1
					-1	500	nA	2
Ii	Input Leakage Current	+Vcc = 18V, -Vcc = -18V, +Vin = +12V, -Vin = -17V	7		- 5	500	nA	1, 2, 3
		+Vcc = 18V, -Vcc = -18V, +Vin = -17V, -Vin = +12V	7		- 5	500	nA	1, 2, 3
Icc+	Power Supply					6	mA	1, 2
	Current					7	mA	3
Icc-	Power Supply Current				- 5		mA	1, 2
					- 6		mA	3
Delta Vio/Delta	Temperature Coefficient Input	25 C ≤ T ≤ 125 C			-25	25	uV/C	2
T	Offset Voltage	-55 C <u><</u> T <u><</u> 25 C			-25	25	uV/C	3
Delta Iio/Delta	Temperature Coefficient Input	25 C ≤ T ≤ 125 C			-100	100	pA/C	2
T	Offset Current	-55 C <u><</u> T <u><</u> 25 C			-200	200	pA/C	3

Voltage Comparator

AS111 RAD-TOL

Austin Semiconductor, Inc.

Electrical Characteristics

USTIN

SEMICONDUCTOR

DC PARAMETERS: (SEE NOTE 8) (Continued)

(The following conditions apply to all the following parameters, unless otherwise specified.) DC: $\pm Vcc$ = $\pm 15V,~Vcm$ = 0V

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Ios	Short Circuit Current	Vout = 5V, t \leq 10mS, Vin- = 0.1V, Vin+ = 0V	3,5			200	mA	1
		·····	3, 5			150	mA	2
			3, 5			250	mA	3
Vio(adj)+	Input Offset Voltage (Adjustment)	Vout = 0V, Vin = 0V, Rs = 50 Ohms	3		5		mV	1
Vio(adj)-	Input Offset Voltage (Adjustment)	Vout = 0V, Vin = 0V, Rs = 50 Ohms	3			- 5	mV	1
Ave+	Voltage Gain (Emitter)	Rl = 600 Ohms	3,6		10		V/mV	4
	(Emile Cer)		3,6		8		V/mV	5,6
Ave- Voltage Gain (Emitter)		3,6		10		V/mV	4	
			3,6		8		V/mV	5,6

AC PARAMETERS: (SEE NOTE 8)

(The following conditions apply to all the following parameters, unless otherwise specified.) AC: $\pm Vcc$ = $\pm 15V,$ Vcm = 0

trLHC	Response Time (Collector	Vod(Overdrive) = -5mV, Cl = 50pF, Vin = -100mV	4		300	nS	7, 8B
Output)		4		640	nS	8A	
trHLC	Response Time (Collector	Vod(Overdrive) = 5mV, Cl = 50pF, Vin = 100mV	4		300	nS	7, 8B
Output)		4		500	nS	8A	

Voltage Comparator

AS111 RAD-TOL

Austin Semiconductor, Inc.

Electrical Characteristics

DC PARAMETERS: DRIFT VALUES

USTIN

SEMICONDUCTOR

(The following conditions apply to all the following parameters, unless otherwise specified.)
DC: ±Vcc = ±15V, Vcm = 0V. "Delta calculations performed on /SPACE devices at group B, subgroup 5
only".

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Vio	Input Offset Voltage	Vin = 0V, Rs = 50 Ohms			-0.5	0.5	mV	1
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50 Ohms			-0.5	0.5	mV	1
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50 Ohms			-0.5	0.5	mV	1
Iib+	Input Bias Current	Vin = 0V, Rs = 50K Ohms			-12.5	12.5	nA	1
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50K Ohms			-12.5	12.5	nA	1
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50K Ohms			-12.5	12.5	nA	1
Iib-	Input Bias Current	Vin = 0V, Rs = 50K Ohms			-12.5	12.5	nA	1
		+Vcc = 29.5V, -Vcc = -0.5V, Vin = 0V, Vcm = -14.5V, Rs = 50K Ohms			-12.5	12.5	nA	1
		+Vcc = 2V, -Vcc = -28V, Vin = 0V, Vcm = +13V, Rs = 50K Ohms			-12.5	12.5	nA	1
Icex	Output Leakage Current	+Vcc = 18V, -Vcc = -18V, Vout = 32V			- 5	5	nA	1

Note 1: Istb = -2mA at -55 C.

Note 2: Calculated parameter.

Note 3: Use DC tape for Ios and Vio(adj), Ave+ and Ave- as indicated in TAPE NAME section of this JRETS.

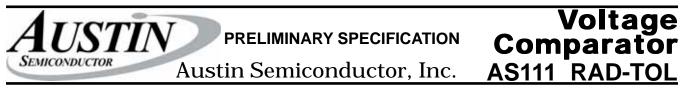
Note 4: Uses AC tape and hardware.

Note 5: Actual min. limit used is 5mA due to test setup.

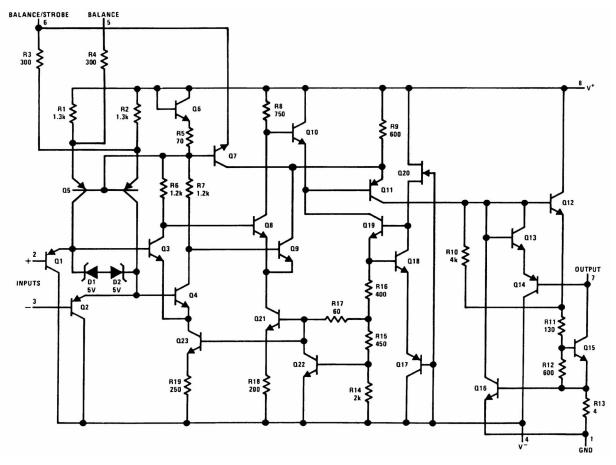
Note 6: Datalog reading in K = V/mV.

Note 7: Vid is voltage difference between inputs.

Note 8: Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table. These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect. Radiaton end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, Method 1019.5, Condition A.



Schematic Diagram²⁰



NOTE 20: Pin connections shown on schematic diagram are for the TO08 can package.

CIRCUIT TECHNIQUES FOR AVOIDING OSCILLATIONS IN COMPARATOR APPLICATIONS

When a high-speed comparator such as the AS111 is used with fast input signals and low source impedances, the output response will normally be fast and stable, assuming that the power supplies have been bypassed (with 0.1 μ F disc capacitors), and that the output signal is routed well away from the inputs (pins 2 and 3) and also away from pins 5 and 6.

However, when the input signal is a voltage ramp or a slow sine wave, or if the signal source impedance is high (1 kW to 100 kW), the comparator may burst into oscillation near the crossing-point. This is due to the high gain and wide bandwidth of comparators like the AS111. To avoid oscillation or instability in such a usage, several precautions are recommended, as shown in Figure 1 below.

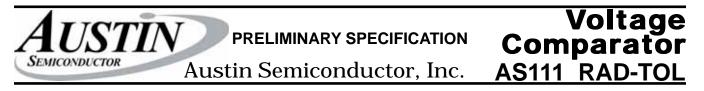
1. The trim pins (pins 5 and 6) act as unwanted auxiliary inputs. If these pins are not connected to a trim-pot, they

should be shorted together. If they are connected to a trimpot, a 0.01 μ F capacitor C1 between pins 5 and 6 will minimize the susceptibility to AC coupling. A smaller capacitor is used if pin 5 is used for positive feedback as in Figure 1.

2. Certain sources will produce a cleaner comparator out put waveform if a 100 pF to 1000 pF capacitor C2 is connected directly across the input pins.

3. When the signal source is applied through a resistive network, R_s , it is usually advantageous to choose an R_s ' of substantially the same value, both for DC and for dynamic (AC) considerations. Carbon, tin-oxide, and metal-film resistors have all been used successfully in comparator input circuitry. Inductive wirewound resistors are not suitable.

(continued)



APPLICATION HINTS (CONTINUED)

4. When comparator circuits use input resistors (eg. summing resistors), their value and placement are particularly important. In all cases the body of the resistor should be close to the device or socket. In other words there should be very little lead length or printed-circuit foil run between comparator and resistor to radiate or pick up signals. The same applies to capacitors, pots, etc. For example, if $R_s=10$ kW, as little as 5 inches of lead between the resistors and the input pins can result in oscillations that are very hard to damp. Twisting these input leads tightly is the only(second best) alternative to placing resistors close to the comparator.

5. Since feedback to almost any pin of a comparator can result in oscillation, the printed-circuit layout should be engineered thoughtfully. Preferably there should be a groundplane under the AS111 circuitry, for example, one side of a double-layer circuit card. Ground foil (or, positive supply or negative supply foil) should extend between the output and the inputs, to act as a guard. The foil connections for the inputs should be as small and compact as possible, and should be essentially surrounded by ground foil on all sides, to guard against capacitive coupling from any high-level signals (such as the output). If pins 5 and 6 are not used, they should be shorted together. If they are connected to a trim-pot, the trim-pot should be located, at most, a few inches away from the AS111, and the 0.01 µF capacitor should be installed. If this capacitor cannot be used, a shielding printed-circuit foil may be advisable between pins 6 and 7. The power supply bypass capacitors should be located within a couple inches of the AS111. (Some other comparators require the

power-supply bypass to be located immediately adjacent to the comparator.)

6. It is a standard procedure to use hysteresis (positive feedback) around a comparator, to prevent oscillation, and to avoid excessive noise on the output because the comparator is a good amplifier for its own noise. In the circuit of Figure 2, the feedback from the output to the positive input will cause about 3 mV of hysteresis. However, if R_s is larger than 100 Ω , such as 50 k Ω , it would not be reasonable to simply increase the value of the positive feedback resistor above 510 k Ω . The circuit of Figure 3 could be used, but it is rather awkward. See the notes in paragraph 7 below.

7. When both inputs of the AS111 are connected to active signals, or if a high-impedance signal is driving the positive input of the AS111 so that positive feedback would be disruptive, the circuit of Figure 1 is ideal. The positive feedback is to pin 5 (one of the offset adjustment pins). It is sufficient to cause 1 to 2 mV hysteresis and sharp transitions with input triangle waves from a few Hz to hundreds of kHz. The positive-feedback signal across the 82 Ω resistor swings 240 mV below the positive supply. This signal is centered around the nominal voltage at pin 5, so this feedback does not add to the V_{OS} of the comparator. As much as 8 mV of V_{OS} can be trimmed out, using the 5 k Ω pot and 3 k Ω resistor as shown.

8. These application notes apply specifically to the AS111 family of comparators, and are applicable to all high-speed comparators in general, (with the exception that not all comparators have trim pins).

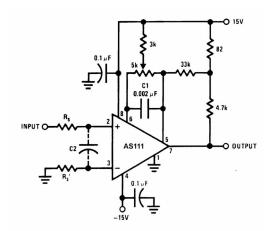
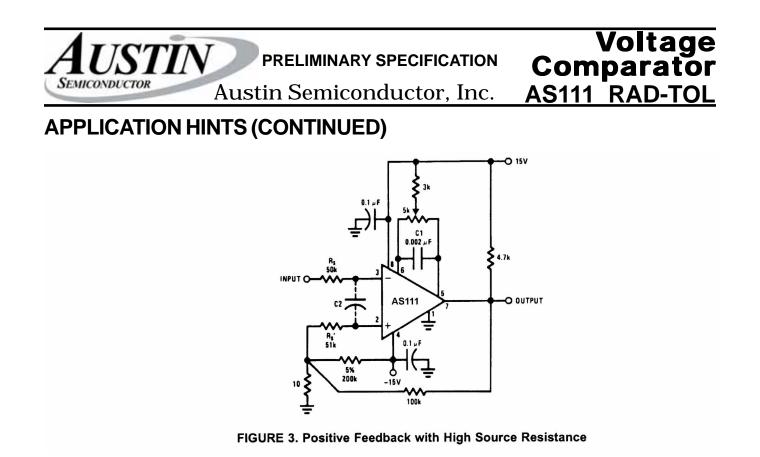


FIGURE 1. Improved Positive Feedback

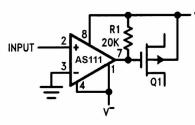


 R_{1} R_{1} R_{2} R_{1} R_{1

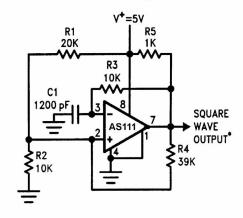
FIGURE 2. Conventional Positive Feedback



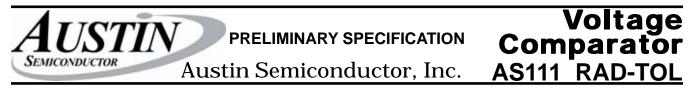
Zero Crossing Detector Driving MOS Switch



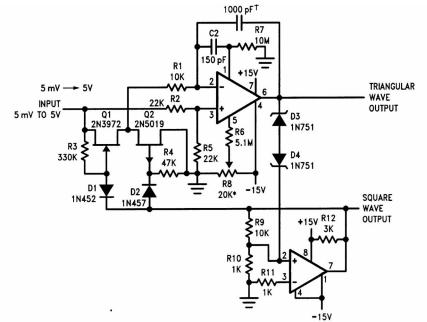
100 kHz Free Running Multivibrator



*TTL or DTL fanout of two

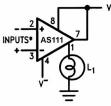


10Hz to 10kHz Voltage Controlled Oscillator

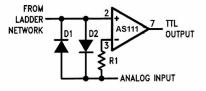


*Adjust for symmetrical square wave time when V_{IN} = 5 mV tMinimum capacitance 20 pF Maximum frequency 50 kHz

Driving Ground-Referred Load

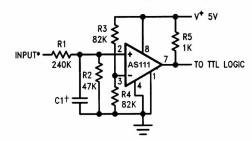


Using Clamp Diodes to Improve Response

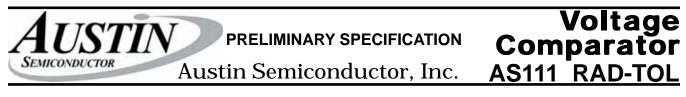


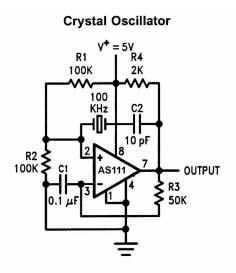
*Input polarity is reversed when using pin 1 as output.

TTL Interface with High Level Logic

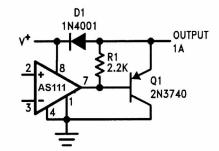


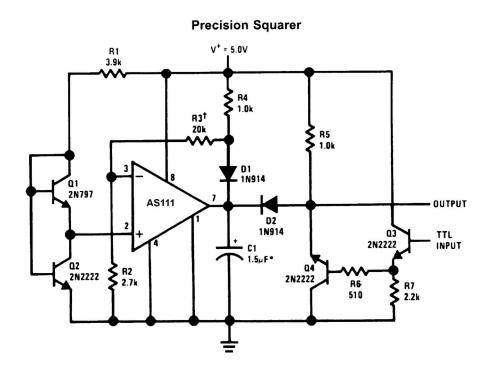
*Values shown are for a 0 to 30V logic swing and a 15V threshold. May be added to control speed and reduce susceptibility to noise spikes.

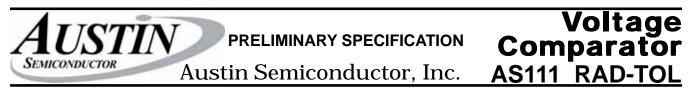




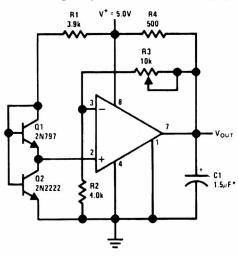




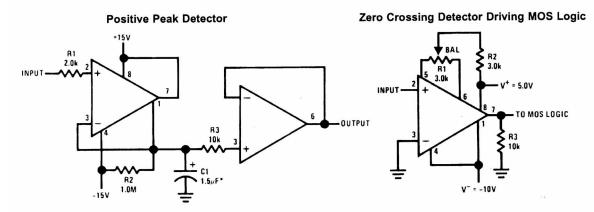




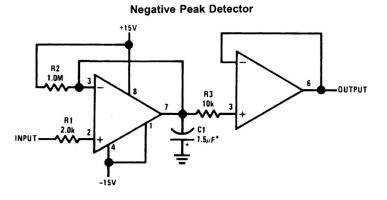
Low Voltage Adjustable Reference Supply



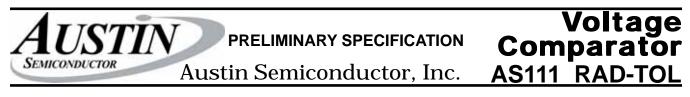
*Solid tantalum



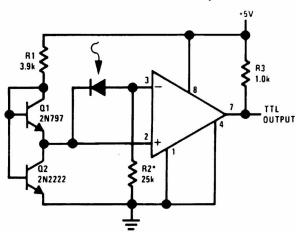
*Solid tantalum



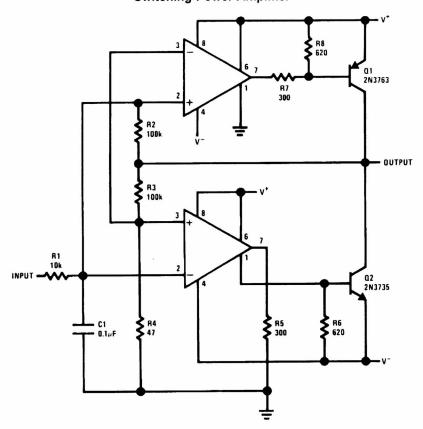
*Solid tantalum



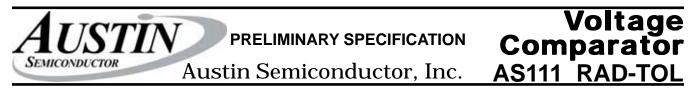
Precision Photodiode Comparator



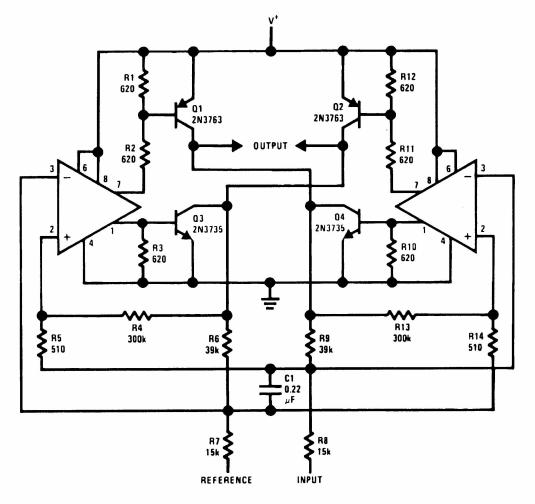
*R2 sets the comparison level. At comparison, the photodiode has less than 5 mV across it, decreasing leakages by an order of magnitude.

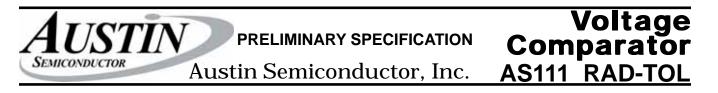


Switching Power Amplifier



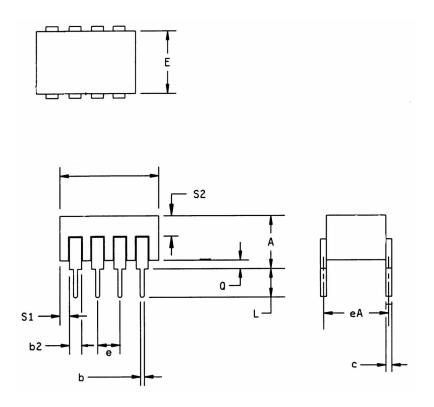
Switching Power Amplifier





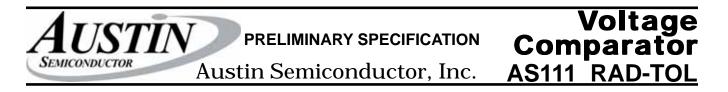
MECHANICAL DEFINITIONS*

ASI Case (Package Designator C008) SMD 5962-00524, Case Outline P (GDIP1-T8)



	ASI SPECIFICATIONS				
SYMBOL	MIN	MAX			
A		0.200			
b	0.014	0.026			
b2	0.045	0.065			
С	0.008	0.018			
D		0.405			
E	0.220	0.310			
е	0.100	BCS			
eA	0.300	BSC			
L	0.125	0.200			
Q	0.015	0.060			
S1	0.005				
S2	0.005				

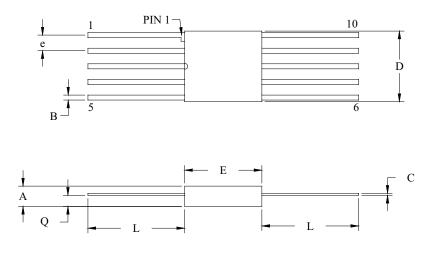
*All measurements are in inches.



MECHANICAL DEFINITIONS*

ASI Case (Package Designator CP10) SMD 5962-00524, Case Outline H

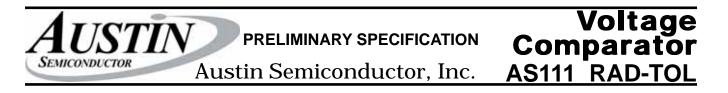
MIL-STD-1835 outline drawing GDFP1-F10



	Min	Max
Α	.045	.085
В	.010	.022
С	.004	.009
D	.226	.251
Е	.235	.260
e	.050	BSC
L	.250	.370
Q	.026	.045

Notes:

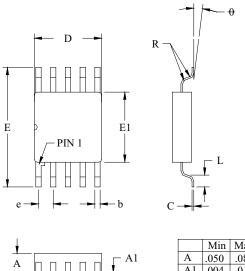
- 1. Lead Finish: Solder dipped with Sn 60 or Sn63 solder conforming to MIL-PRF-38535 to a min thickness of 200 micro-inches. Solder may be applied over lead base metal or Sn plate. Max limit may be increased by .003 inches after lead finish applied.
- 2. Lead 1 identification shall be:
- a) A notch or other mark within this area.
- b) a TAB on lead 1, either side.



MECHANICAL DEFINITIONS*

ASI Case (Package Designator GW10) SMD 5962-00524, Case Outline Z

MIL-STD-1835 outline drawing GDFP1-G10



	Min	Max
Α	.050	.080
A1	.004	.012
b	.015	.022
С	.004	.009
D	.228	.253
E	.400	.420
E1	.235	.260
e	.050 I	BSC
L	.037	.043
R	.013	.017
θ	0	7

Notes:

1. Lead Finish: Solder dipped with Sn 60 or Sn63 solder conforming to MIL-PRF-38535 to a min thickness of 200 micro-inches. Solder may be applied over lead base metal or Sn plate. Max limit may be increased by .003 inches after lead finish applied.

2. Lead 1 identification shall be:

a) A notch or other mark within this area.

b) a TAB on lead 1, either side.



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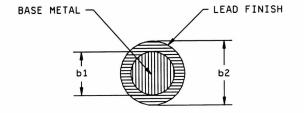
2

D

D1

F

Δ



SECTION A-A

	ASI SPECIFICATIONS				
SYMBOL	MIN	MAX			
A	0.165	0.185			
b	0.016	0.019			
b1	0.016	0.021			
b2	0.016	0.024			
D	0.335	0.375			
D1	0.305	0.335			
D2	0.110	0.160			
е	0.200 BSC				
e1	0.100) BSC			
F		0.040			
k	0.027	0.034			
k1	0.027	0.045			
L	0.500	0.750			
L1		0.050			
L2	0.250				
Q	0.010	0.045			
α	45°	BSC			
β	45°	BSC			

*All measurements are in inches. AS111 RAD-TOL k 1

Austin Semiconductor, Inc.

Voltage Comparator AS111 RAD-TOL

ORDERING INFORMATION

EXAMPLE: AS111C008/XT

STIN

SEMICONDUCTOR

Device Number	RAD Level	Package Type	Process
AS111	P,R, or blank	C008	/*

EXAMPLE: AS111PCP10/883C

Device Number	RAD Level	Package Type	Process
AS111	P,R, or blank	CP10	/*

EXAMPLE: AS111PGW10/SPACE

Device Number	RAD Level	Package Type	Process
AS111	P,R, or blank	GW10	/*

EXAMPLE: AS111RTO99/SPACE

Device Number	RAD Level	Package Type	Process
AS111	P,R or blank	TO99	/*

+ RADIATION Levels:

BLANK = No Radiation Guarantee

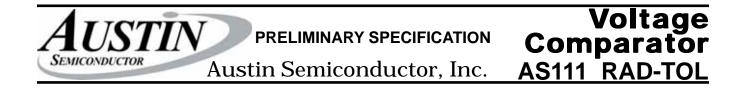
P = 30K Rads(Si) Total Dose

R = 100K Rads(Si) Total Dose

*AVAILABLE PROCESSES:

XT = Extended Temperature Range	-55°C to +125°C
/ 883C = MIL-STD-883 paragraph 1.2.1	-55°C to +125°C
/ SPACE = MIL-STD-883 para 1.2.1	-55°C to +125°C

NOTE: ASI supports Customer specified drawings (SCDs), please contact your SALES or Factory Representative for information.



ASI TO DSCC PART NUMBER CROSS REFERENCE

ASI PART NUMBER

DSCC PART NUMBER

DSCC part numbers pending, contact your ASI Sales or factory rep for updated status.

* ASI part number is for reference only. Orders received referencing the SMD part number will be processed per the SMD.